

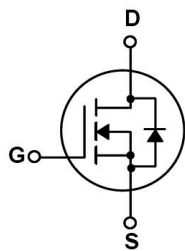
/ Descriptions

/ Features

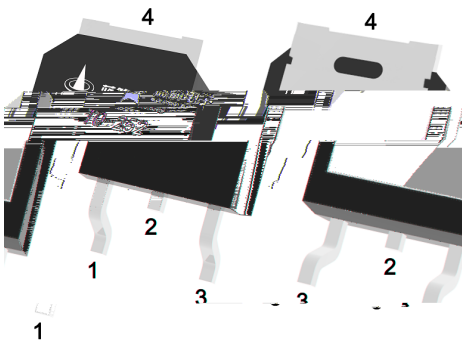
$\leq$	Ω	Ω
$\leq$	Ω	Ω

/ Applications

/ Equivalent Circuit



/ Pinning



/ Marking

/ Absolute Maximum Ratings(Tc=25)

/ Electrical Characteristics(Tc=25)

		μ				
						μ
						Ω
						μ

/ Electrical Characteristics(Tc=25)

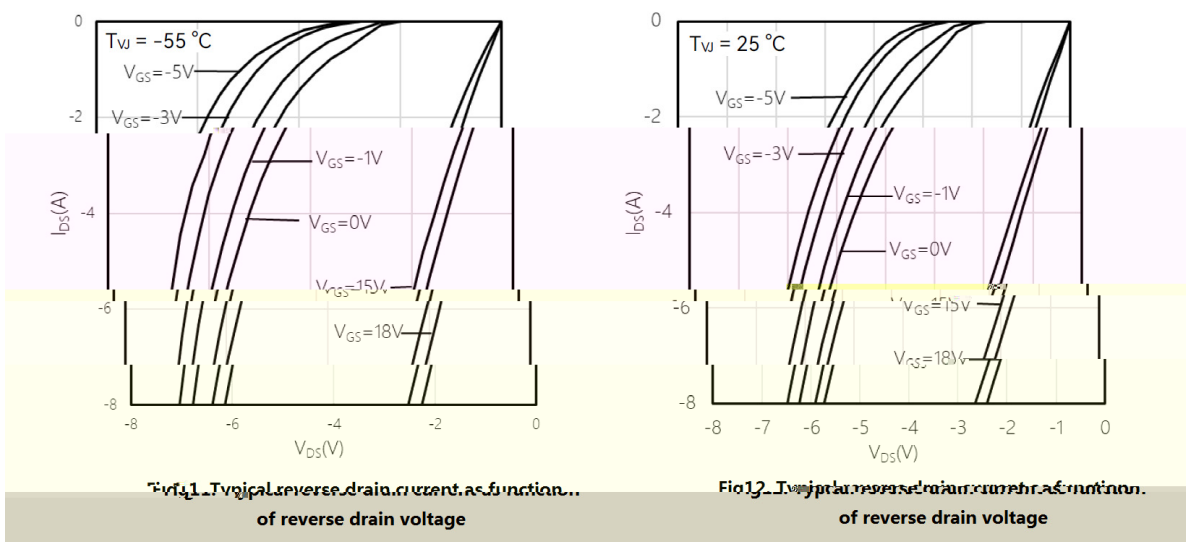
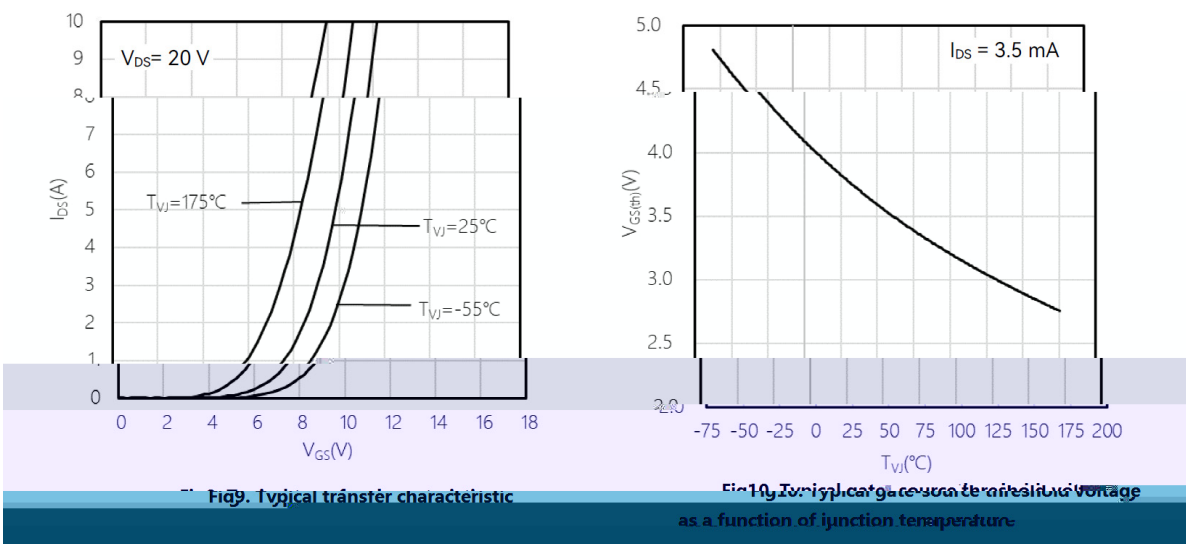
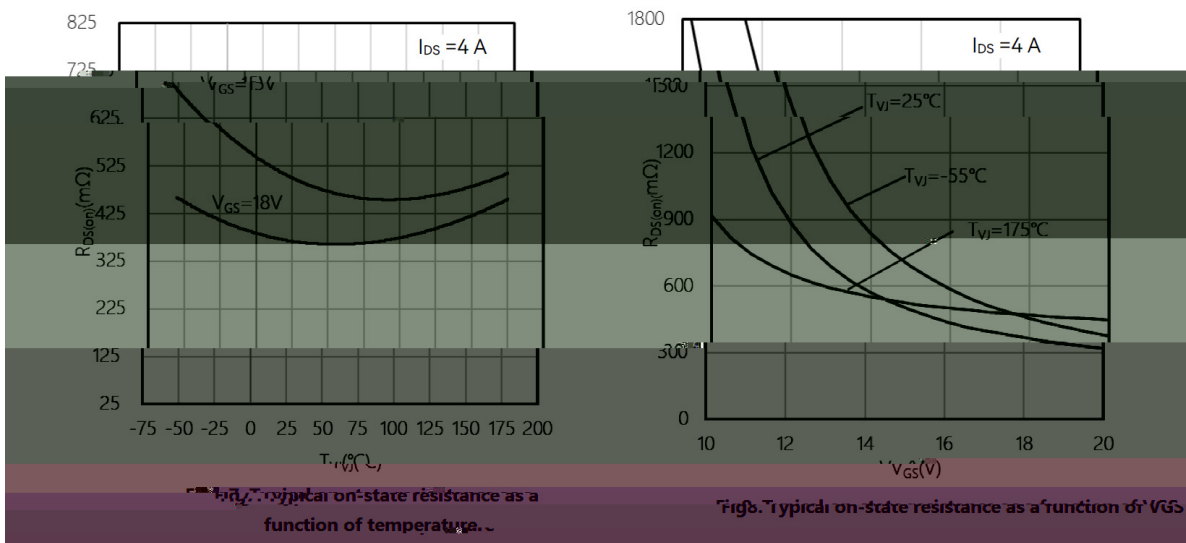
		Ω μ				
-						
-						μ
						Ω

BRSC65R600ZDP



DATA SHEET

/ Electrical Characteristic Curve



/ Electrical Characteristic Curve

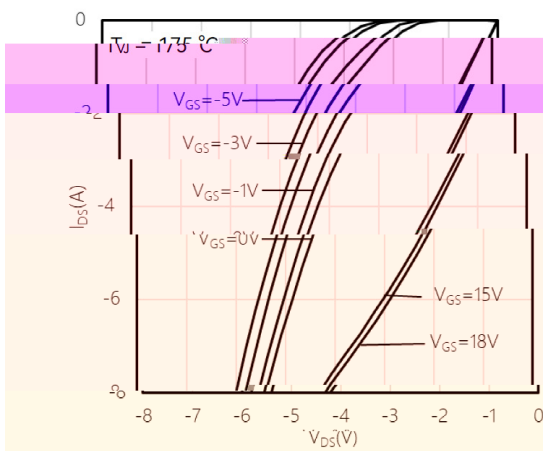


Fig13. Typical reverse drain current as function of reverse drain voltage

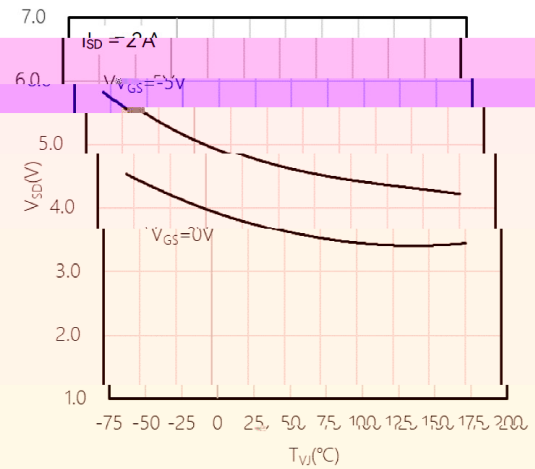


Fig14. Typical reverse drain voltage as function of junction temperature

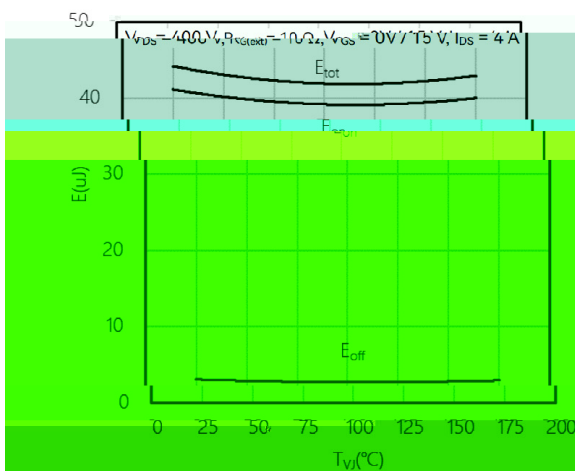


Fig15. Typical switching energy as a function of junction temperature, 2nd device own body diode: VGS = 0V

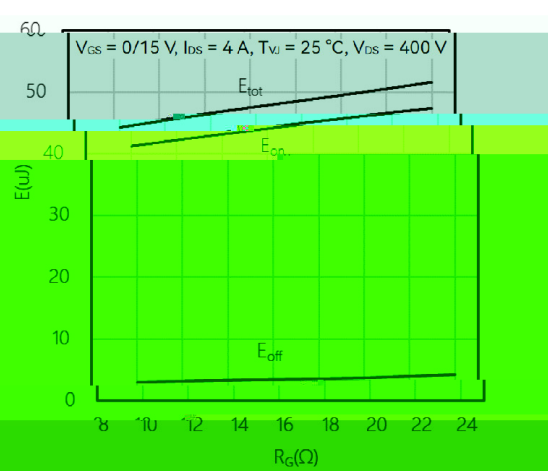


Fig16. Typical switching energy as a function of gate resistance, 2nd device own body diode: VGS = 0V

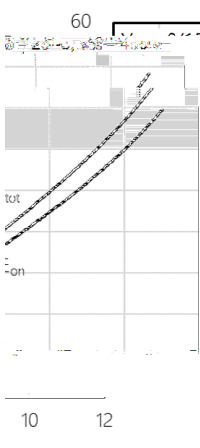


Fig17. Typical switching energy losses as a function of gate resistance, 2nd device own body diode: VGS = 0V

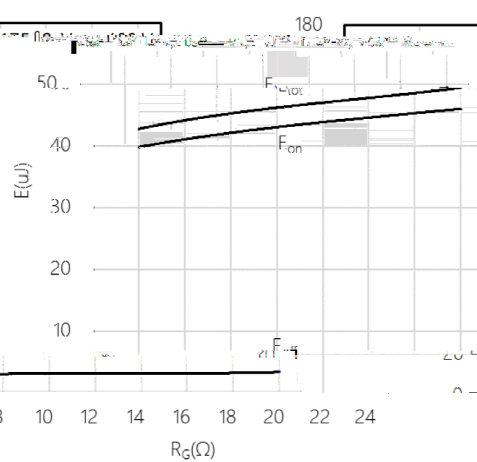


Fig17. Typical switching energy losses as a function of gate resistance, 2nd device own body diode: VGS = 0V

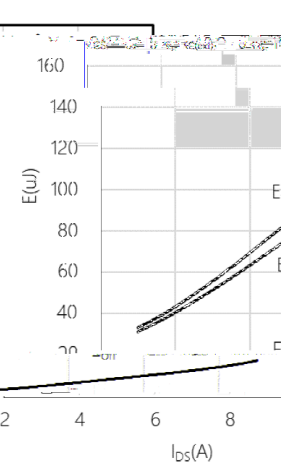
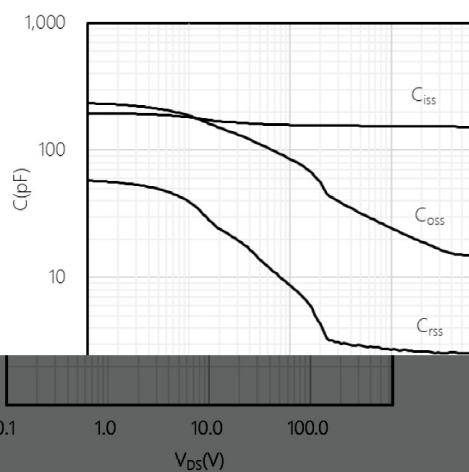
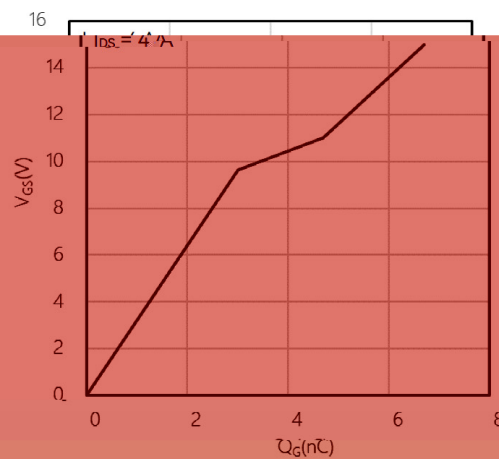
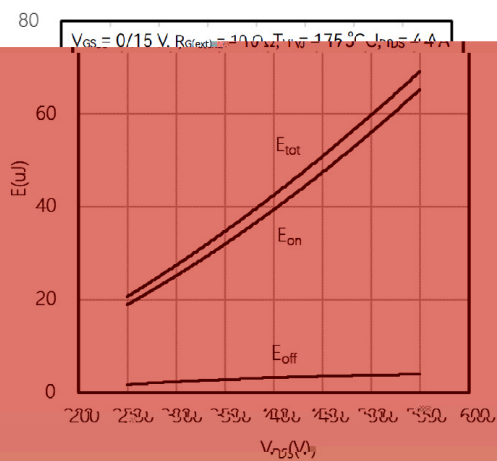
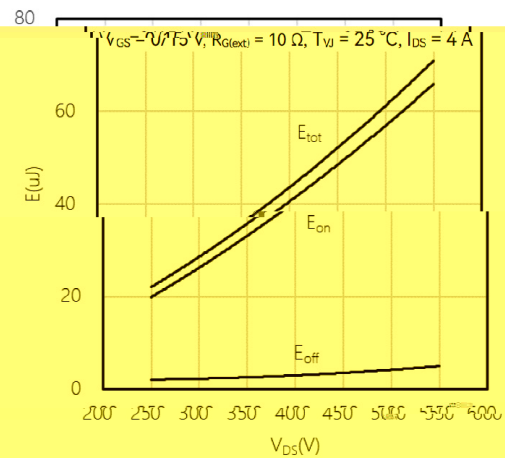
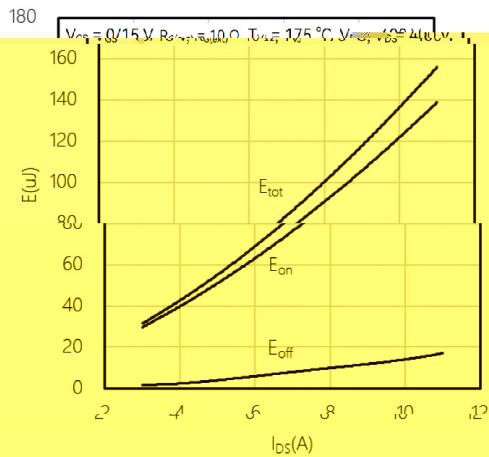


Fig18. Typical switching energy losses as a function of Ids, 2nd device own body diode: VGS = 0V

/ Electrical Characteristic Curve



/ Electrical Characteristic Curve

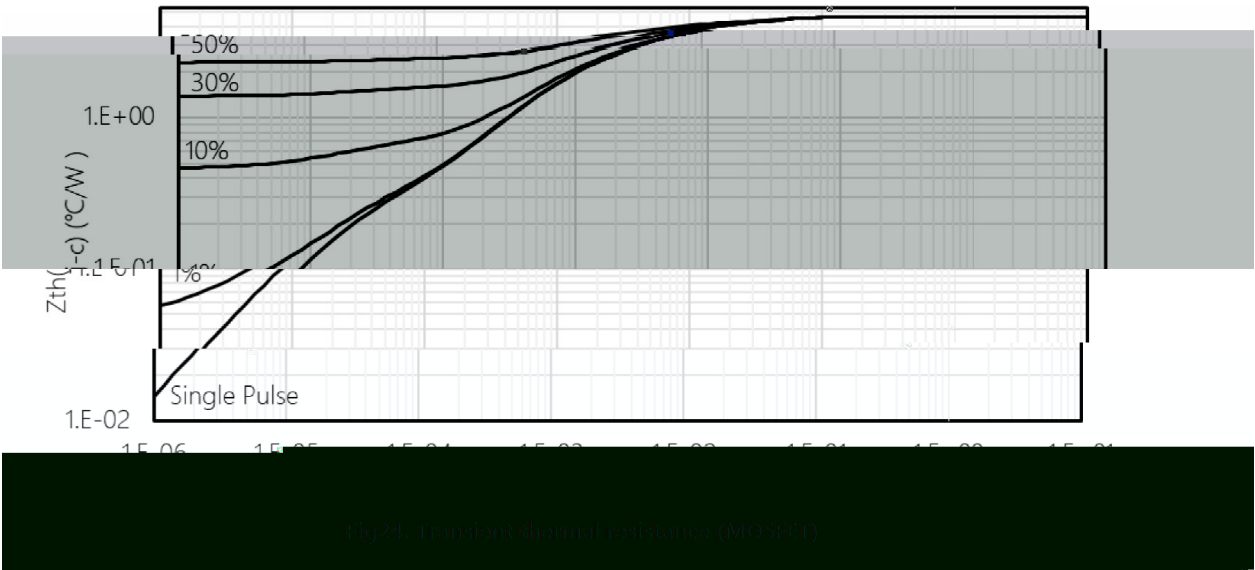
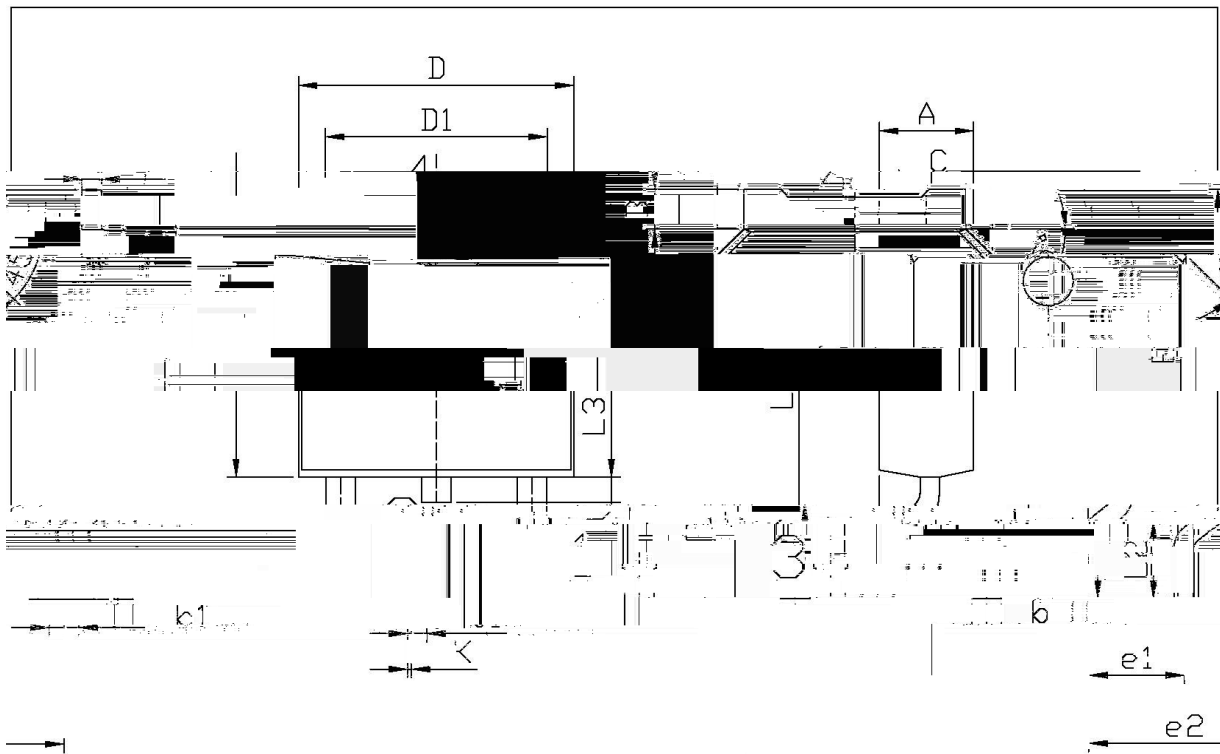


Fig.24. Transient thermal impedance (MOSFET)

/ Package Dimensions

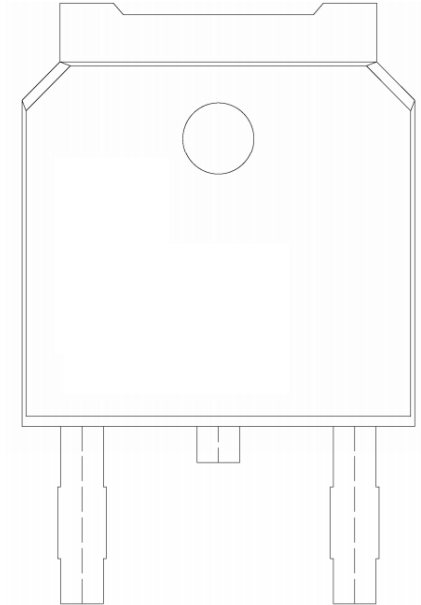


单位: mm

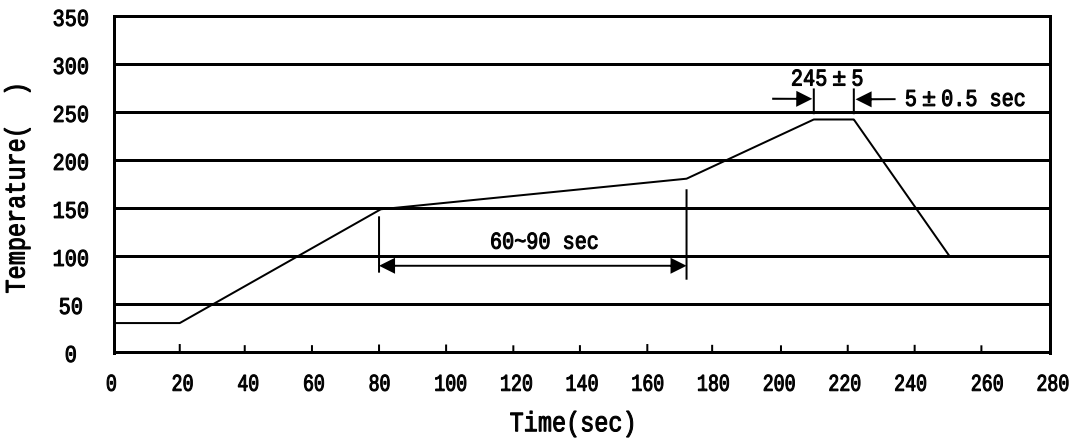
Symbol		Dimensions In Millimeters		Symbol		Dimensions In Millimeters	
		Min	Max			Min	Max
40	E	5.95	6.25	A		2.20	2.54
25	e1	2.24	2.34	B		0.95	1.27
0.50	e2	4.13	4.73	b		0.70	0.95
0.55	L1	9.85	10.35	b1		0.45	0.70
0.45	C	0.45	0.55	D		1.70	2.00
0.60	L3	0.60	0.90	D1		6.45	6.73
5.50	K	0.00	0.10				

T0-252

/ Marking Instructions



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/ Resistance to Soldering Heat Test Conditions

/ Packaging SPEC.

/ Notices